

TOOT 3559660

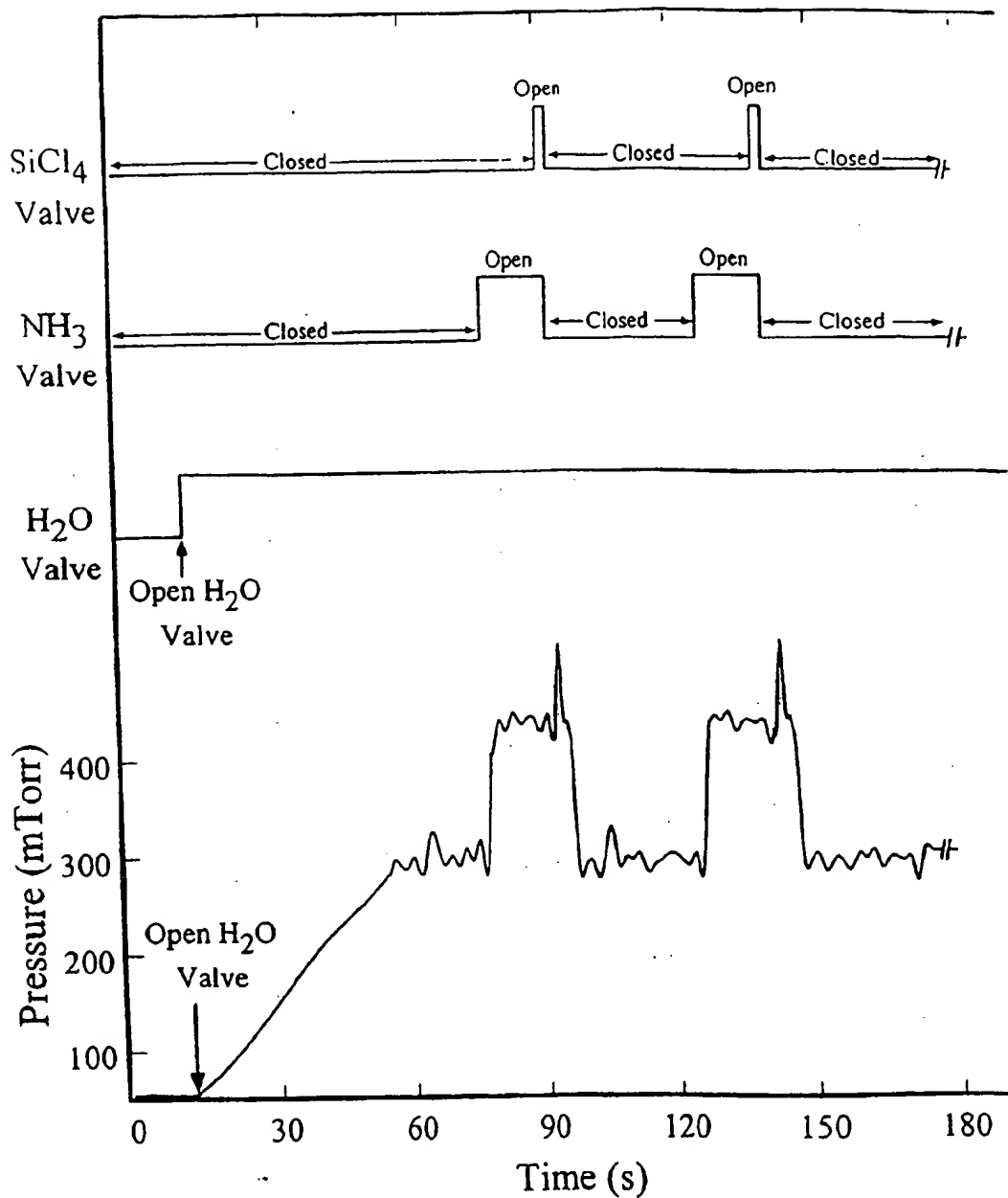


Fig. 1

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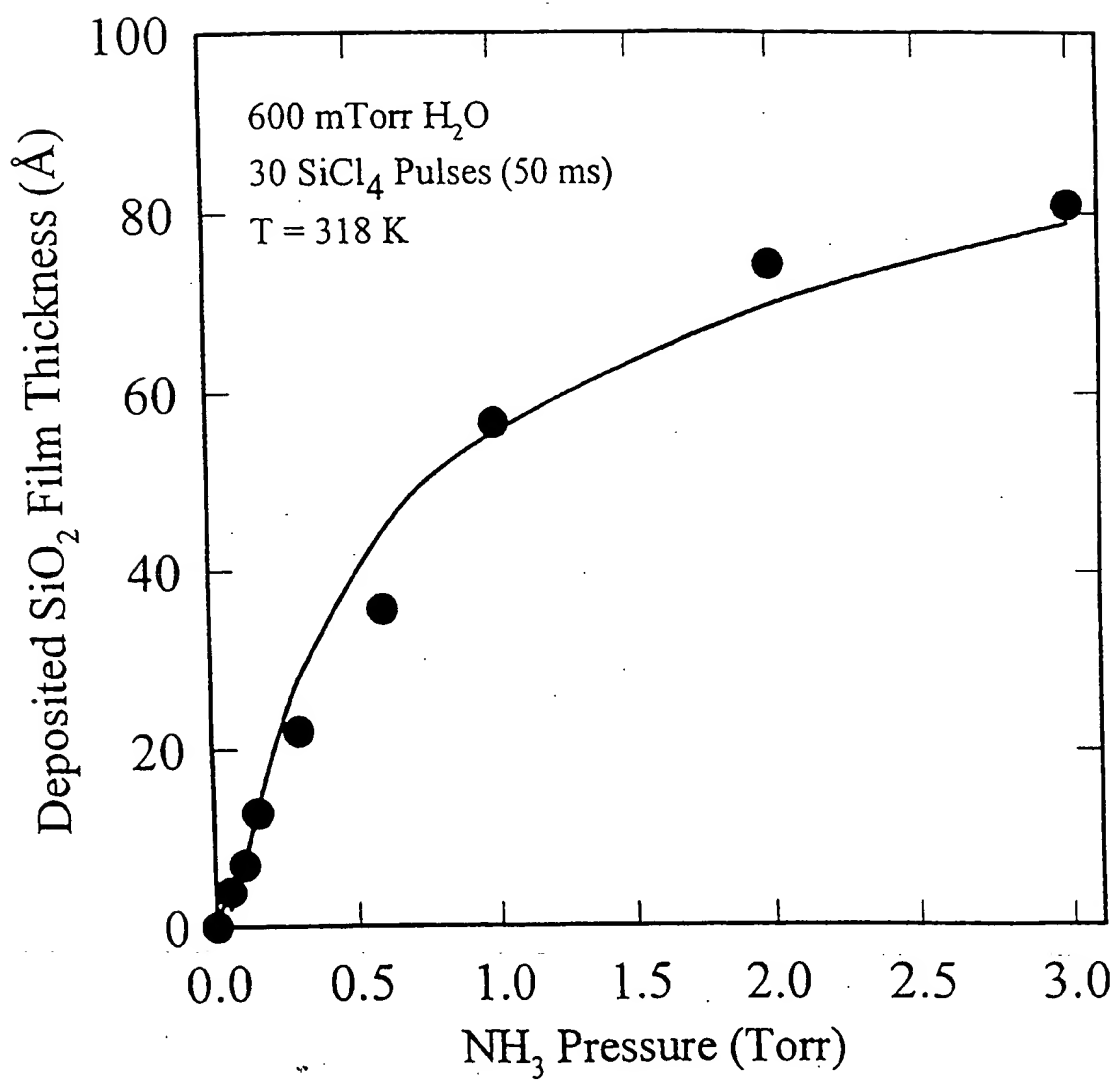


Fig. 2

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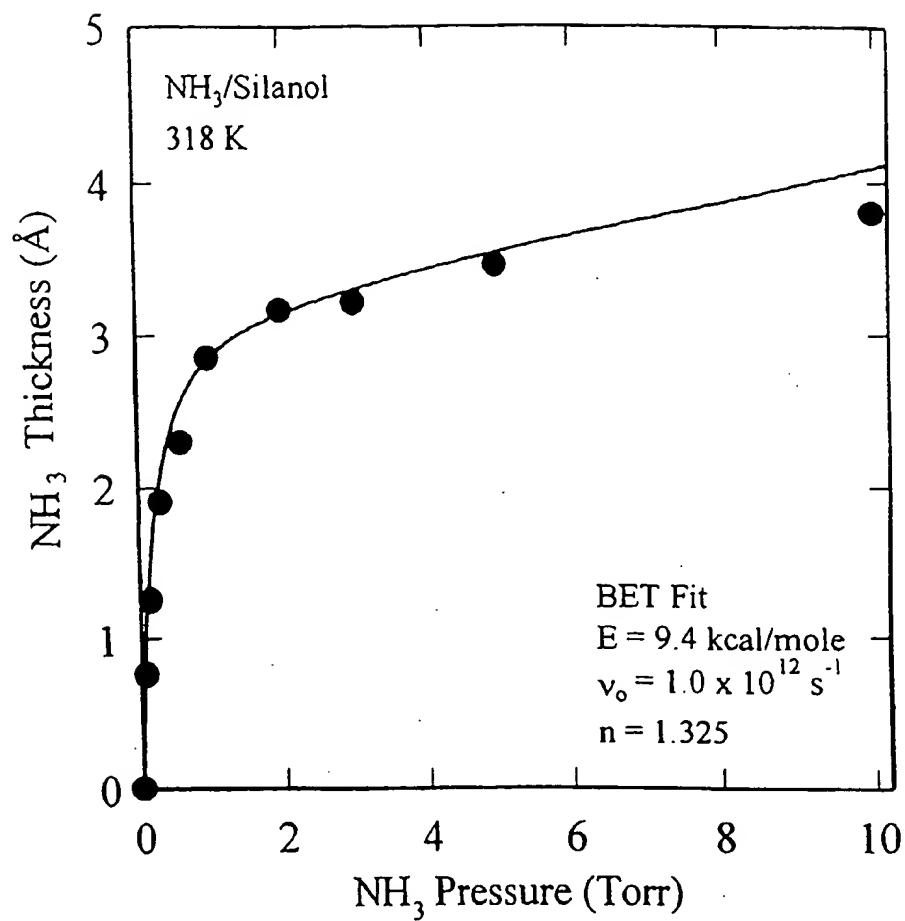


Fig. 3

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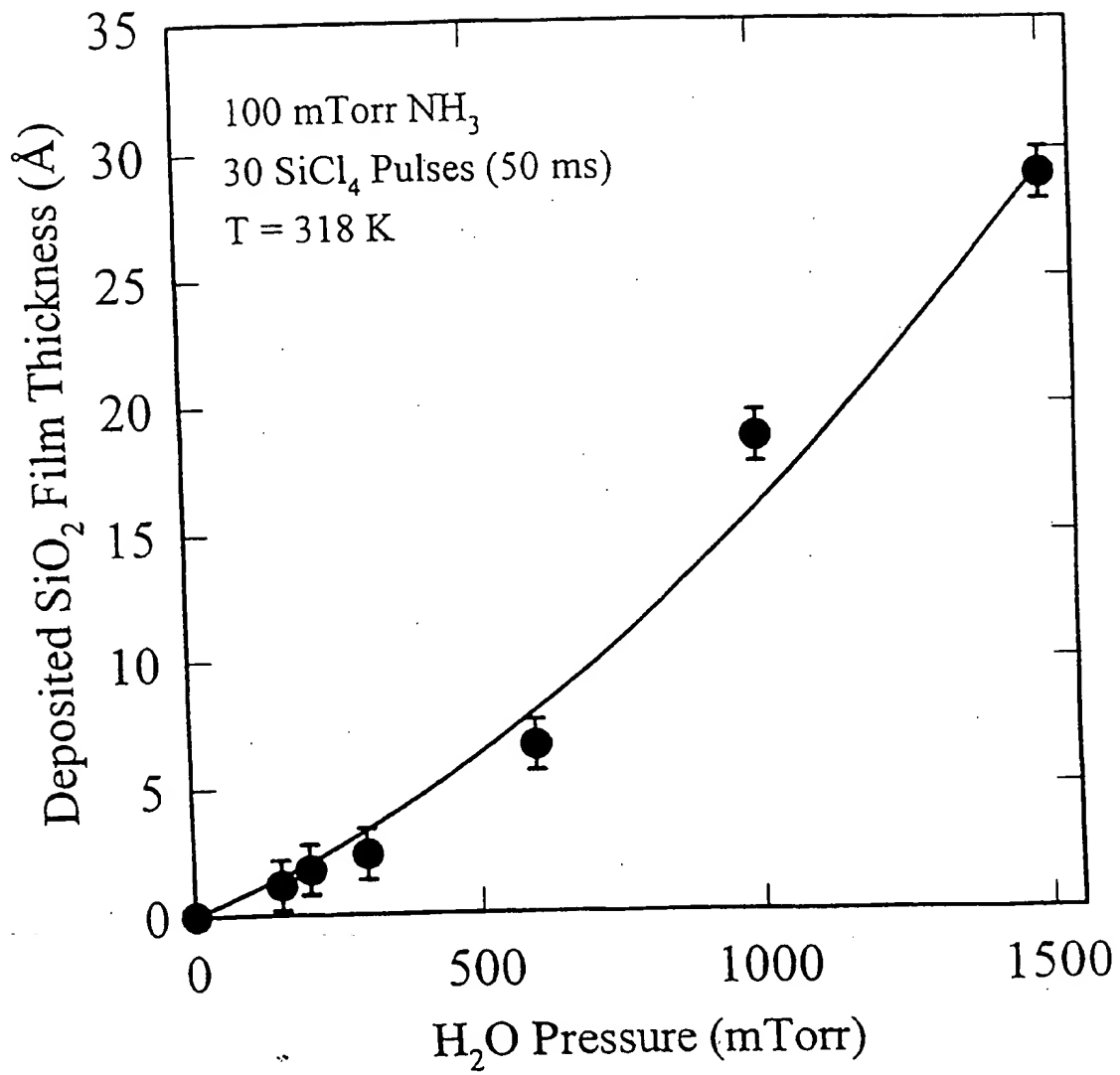


Fig. 4

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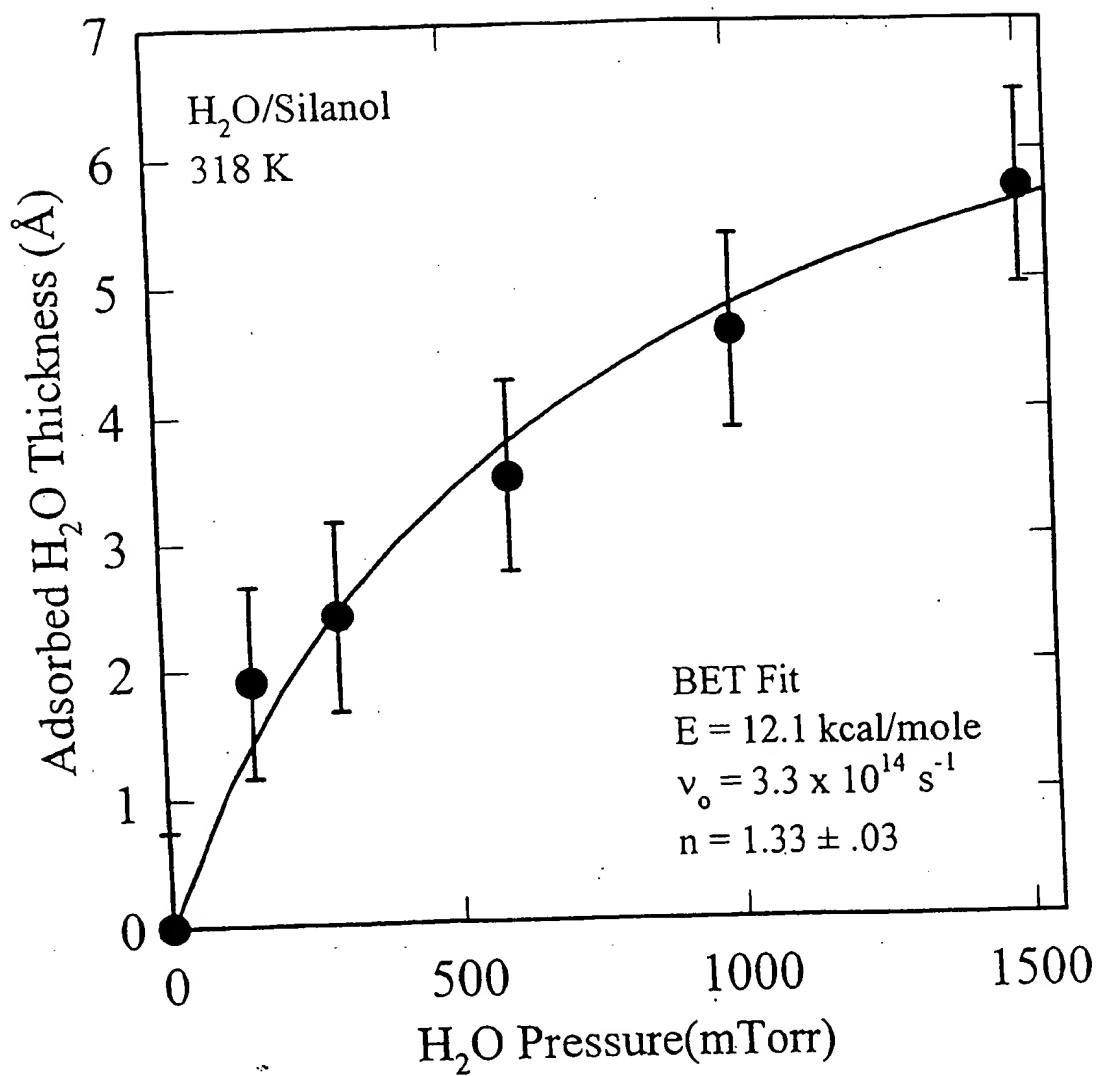


Fig. 5

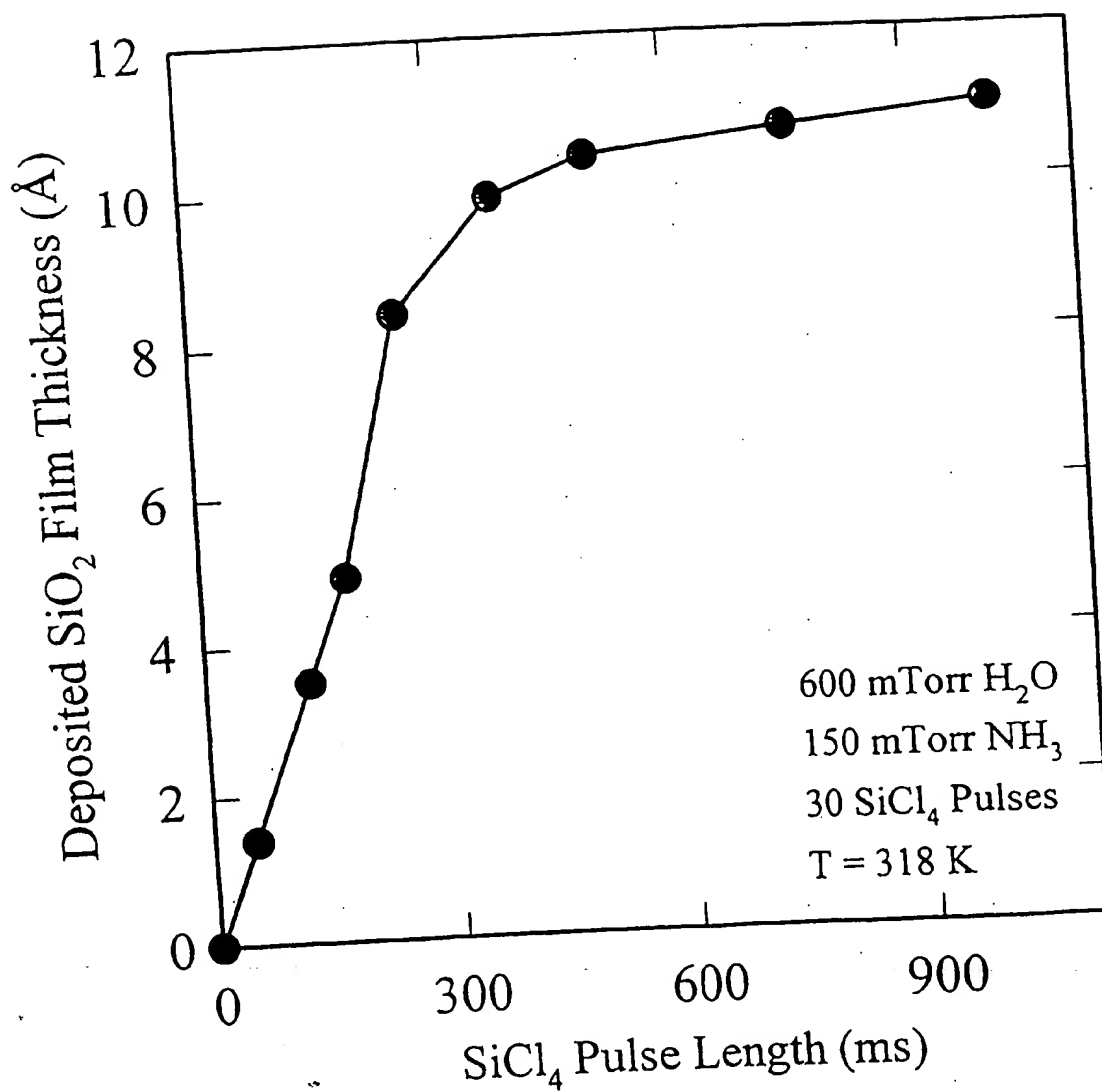


Fig. 6

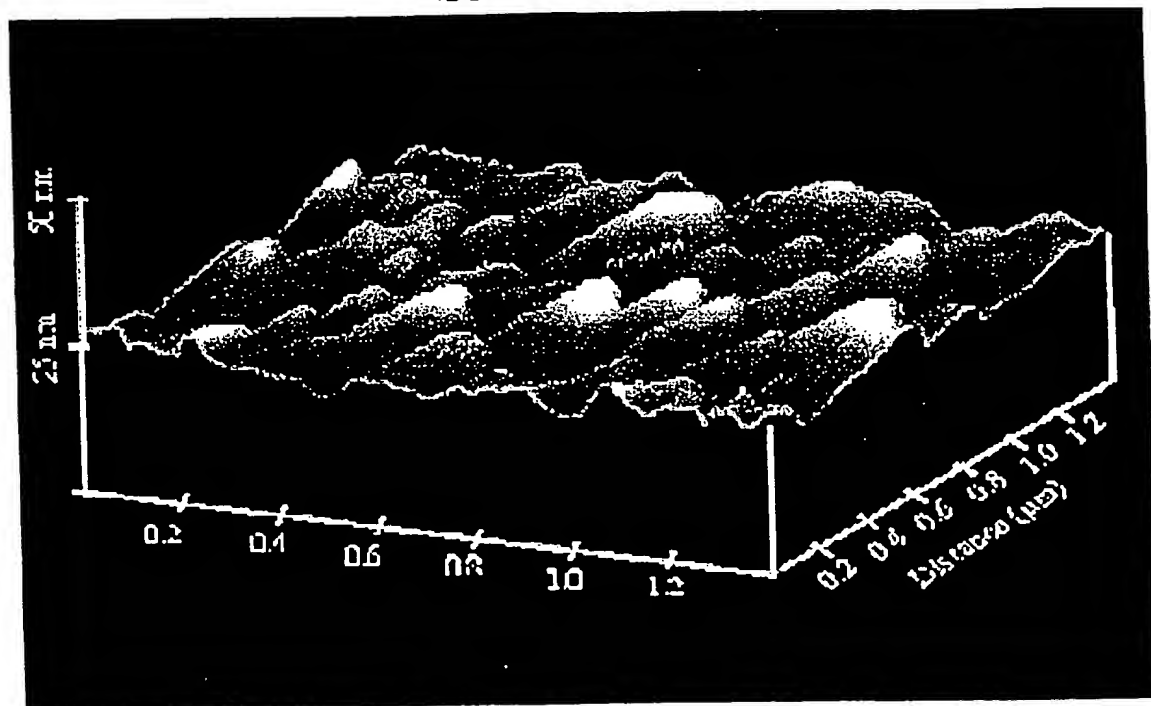
A line graph showing the relationship between the number of SiCl_4 pulses and the total SiO_2 film thickness. The x-axis is labeled 'Number of SiCl_4 Pulses' and ranges from 0 to 300. The y-axis is labeled 'Total SiO_2 Film Thickness (\AA)' and ranges from 0 to 90. The graph shows a linear increase in film thickness with the number of pulses. The data points are connected by a solid line. The conditions for the experiment are: 100 mTorr NH_3 , 300 mTorr H_2O , SiCl_4 Pulse (50 ms), and $T = 318 \text{ K}$.

Number of SiCl_4 Pulses	Total SiO_2 Film Thickness (\AA)
0	4
25	12
50	18
75	26
100	33
125	39
150	46
175	52
200	58
225	64
250	70

Fig. 7

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Side View



Top View

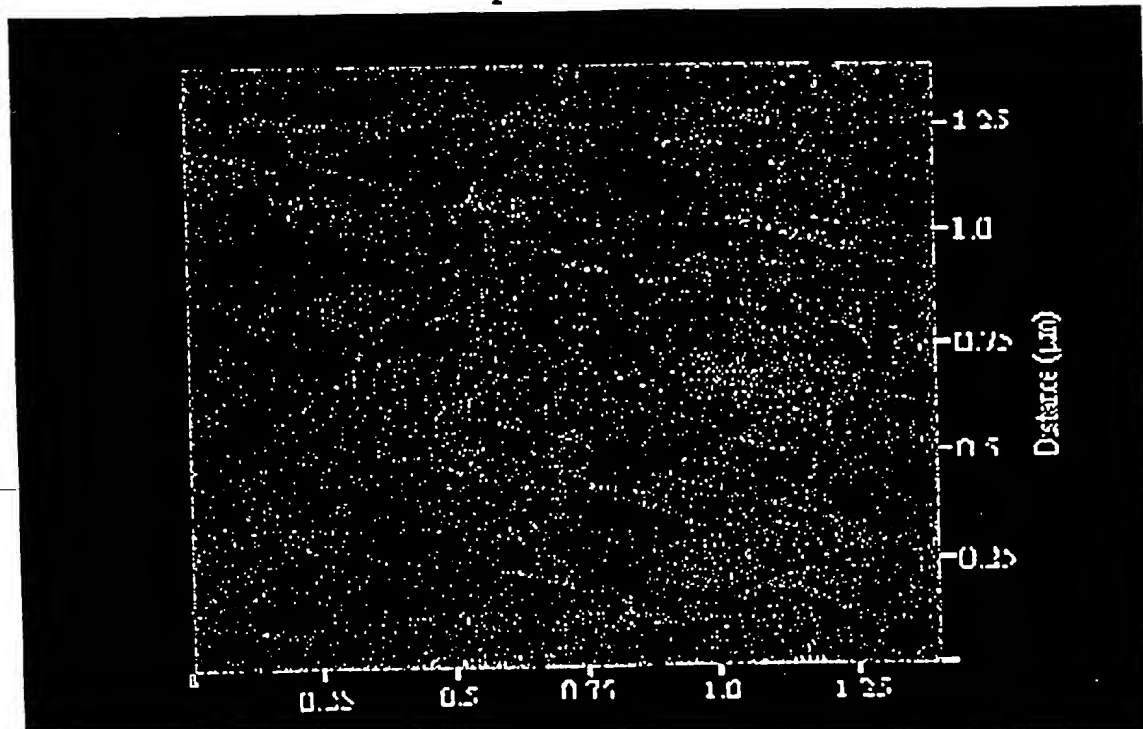


Fig. 8

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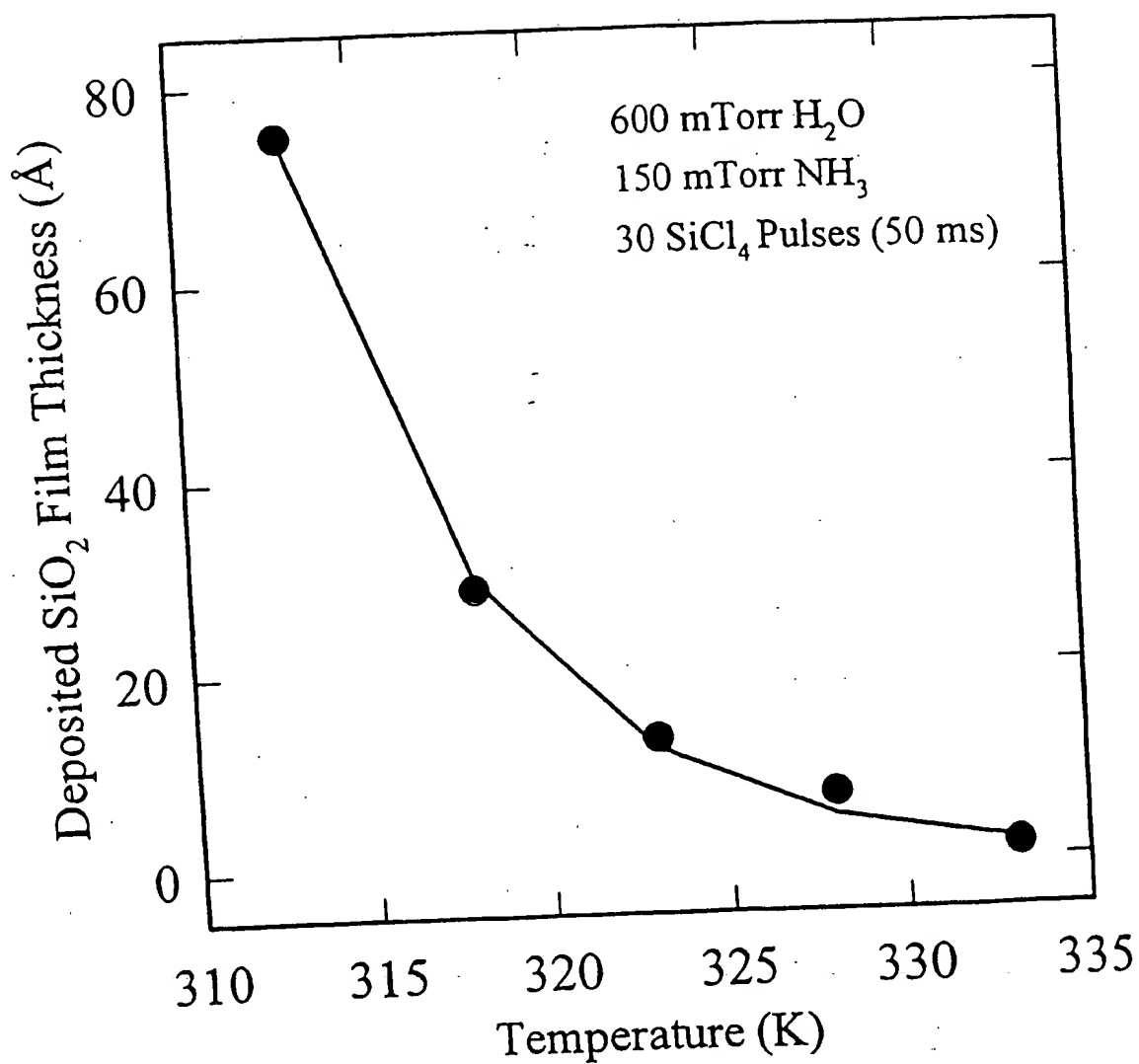


Fig. 9

